

# Phase Control Thyristors (Hockey PUK Version), 1350 A



**B-PUK (TO-200AC)** 

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> 1350 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 600 V				
V <sub>TM</sub>	1.31 V				
I <sub>GT</sub>	100 mA				
T <sub>J</sub>	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1350	А			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		2700	А			
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C			
1	50 Hz	24 400	А			
ITSM	60 Hz	25 600	A			
l <sup>2</sup> t	50 Hz	2986	kA <sup>2</sup> s			
1-1	60 Hz	2726	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V			
t <sub>q</sub>	Typical	150	μs			
TJ		-40 to 125	°C			

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA					
VS-ST780CL	04	400 500		80					
V3-31760UL	06	600	700	00					



ABSOLUTE MAXIMUM RATINGS	S						
PARAMETER	SYMBOL		VALUES	UNITS			
Maximum average on-state current	1	180° condu	ction, half sine v	vave	1350 (500)	Α	
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	2700		
		t = 10 ms	No voltage		24 400	A	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		25 600		
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial $T_J = T_J$ maximum	20 550		
		t = 8.3 ms	reapplied		21 500	]	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied 100 % V <sub>RRM</sub> reapplied		2986	- kA <sup>2</sup> s	
		t = 8.3 ms			2726		
waximum i-t for fusing		t = 10 ms			2112		
		t = 8.3 ms			1928		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	ms, no voltage	reapplied	29 860	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.80	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			]	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.14	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.13	11122	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 3600 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.31	V	
Maximum holding current	l <sub>Η</sub>	T 05 °C anada supply 10 V registive lead		600	mA		
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	IIIA	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs			
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0				
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 750 A, $T_J$ = $T_J$ maximum, dl/dt = 60 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	150	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PANAMETEN	STIVIBOL	TES	SI CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10.0		w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50  Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T. T			.0	V
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			5.0	
		T <sub>J</sub> = -40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode	200	-	
DC gate current required to trigger	$I_{GT}$	T <sub>J</sub> = 25 °C		100	200	mA
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = -40 °C		2.5	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.1	-	
DC gate current not to trigger	$I_{GD}$		Maximum gate	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal registeres innation to heateigh	В	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.031	K/W		
Maximum thermal resistance, case to heatsink	В	DC operation single side cooled	0.011			
Maximum thermal resistance, case to neatsink	$R_{thC-hs}$	DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)		

△R <sub>thJ-hs</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_{J} = T_{J}$ maximum		
120°	0.011	0.011	0.011	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

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## Vishay Semiconductors

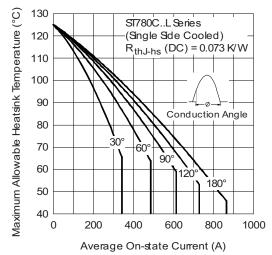


Fig. 1 - Current Ratings Characteristics

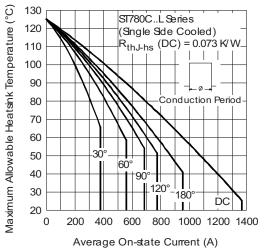


Fig. 2 - Current Ratings Characteristics

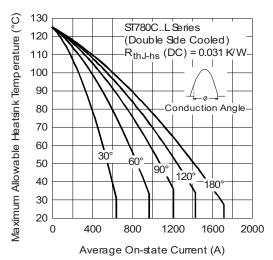


Fig. 3 - Current Ratings Characteristics

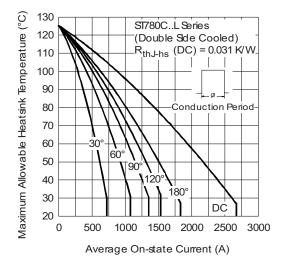


Fig. 4 - Current Ratings Characteristics

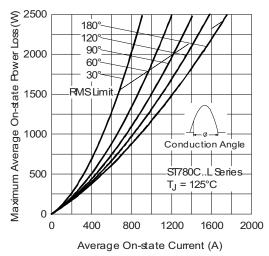


Fig. 5 - On-State Power Loss Characteristics

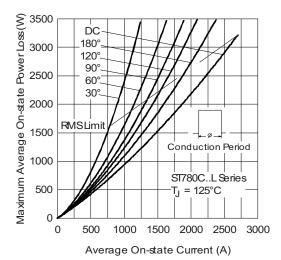


Fig. 6 - On-State Power Loss Characteristics

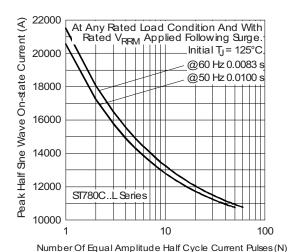


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

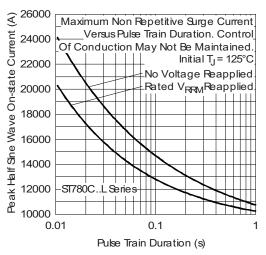


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

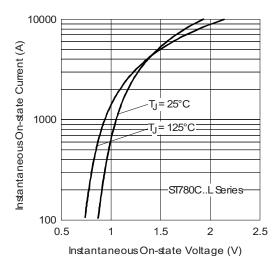


Fig. 9 - On-State Voltage Drop Characteristics

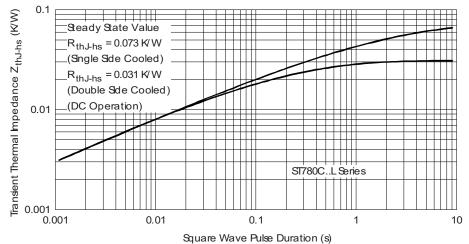


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

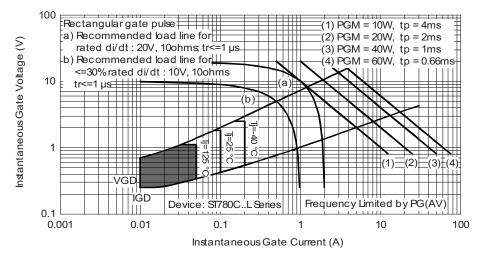
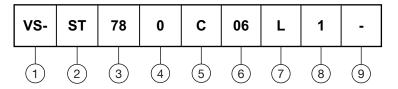


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

#### **Device code**



Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/μs (standard selection)

• L = 1000 V/µs (special selection)

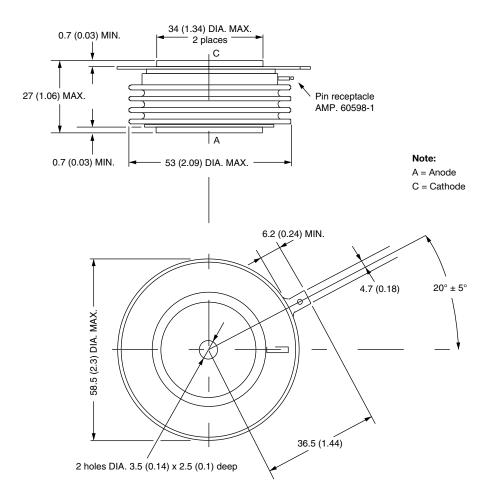
LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95076			



# **B-PUK (TO-200AC)**

### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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